Development Board EPC9060/61 Quick Start Guide Half-bridge with Gate Drive for EPC2030/31

Revision 2.0

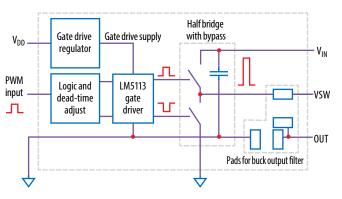


DESCRIPTION

These development boards are in a half-bridge topology with onboard gate drives, featuring the EPC2030/31 eGaN[®] field effect transistors (FETs). The purpose of these development boards is to simplify the evaluation process of these eGaN FETs by including all the critical components on a single board that can be easily connected into any existing converter.

The development board is 2" x 2" and contains two eGaN FETs in a half-bridge configuration using the Texas Instruments LM5113 gate driver, supply and bypass capacitors. The board contains all critical components and layout for optimal switching performance and has additional area to add buck output filter components on the board. There are also various probe points to facilitate simple waveform measurement and efficiency calculation. A complete block diagram of the circuit is given in figure 1.

For more information on the EPC2030 and EPC2031 eGaN FETs, please refer to the datasheets available from EPC at www.epc-co.com. The datasheet should be read in conjunction with this quick start guide.





Symbol	Parameter	Conditions	Min	Мах	Units
V _{DD}	Gate Drive Input Supply Range		7	12	V
	Due le suit Velte se Dense	When using 40 V devices, EPC9060		32 ⁽¹⁾	v
V _{IN}	Bus Input Voltage Range	When using 60 V devices, EPC9061		48(1)	V
V	Switch Node Output Voltage	When using 40 V devices, EPC9060		40	V
V _{OUT}	Switch Node Output Voltage	When using 60 V devices, EPC9061		60	V
	Switch Nodo Output Current	When using 40 V devices, EPC9060		25 ⁽¹⁾	А
lout	Switch Node Output Current	When using 60 V devices, EPC9061		24 ⁽¹⁾	А
V _{PWM}	PWM Logic Input Voltage Threshold	Input 'Low'	3.5	6	V
		Input 'High'	0	1.5	v
	Minimum "High" State Input Pulse Width	V _{PWM} rise and fall time < 10ns	50		ns
	Minimum "Low" State Input Pulse Width	V _{PWM} rise and fall time < 10ns	100 ⁽²⁾		ns

Table 1: Performance Summary ($T_A = 25 \text{ °C}$) EPC9060/61

 Assumes inductive load, maximum current depends on die temperature – actual maximum current with be subject to switching frequency, bus voltage and thermal cooling.

(2) Limited by time needed to 'refresh' high side bootstrap supply voltage.

QUICK START PROCEDURE

The development boards are easy to set up to evaluate the performance of the eGaN FET. Refer to figure 2 for proper connect and measurement setup and follow the procedure below:

- 1. With power off, connect the input power supply bus to $+V_{IN}$ (J5, J6) and ground / return to $-V_{IN}$ (J7, J8).
- 2. With power off, connect the switch node of the half-bridge OUT (J3, J4) to your circuit as required.
- With power off, connect the gate drive input to +V_{DD} (J1, Pin-1) and ground return to -V_{DD} (J1, Pin-2).
- 4. With power off, connect the input PWM control signal to PWM (J2, Pin-1) and ground return to any of the remaining J2 pins.
- 5. Turn on the gate drive supply make sure the supply is between 7 V and 12 V range.
- Turn on the bus voltage to the required value (do not exceed the absolute maximum voltage on V_{OUT} as indicated in the table below:
 - a. EPC9060, 40 V
 - b. EPC9061, 60 V
 - 7. Turn on the controller / PWM input source and probe switching node to see switching operation.
- 8. Once operational, adjust the bus voltage and load PWM control within the operating range and observe the output switching behavior, efficiency and other parameters.
- 9. For shutdown, please follow steps in reverse.

NOTE. When measuring the high frequency content switch node (OUT), care must be taken to avoid long ground leads. Measure the switch node (OUT) by placing the oscilloscope probe tip through the large via on the switch node (designed for this purpose) and grounding the probe directly across the GND terminals provided. See figure 3 for proper scope probe technique.

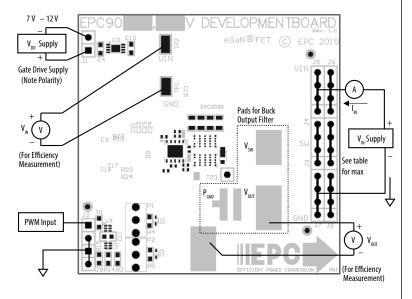


Figure 2: Proper Connection and Measurement Setup

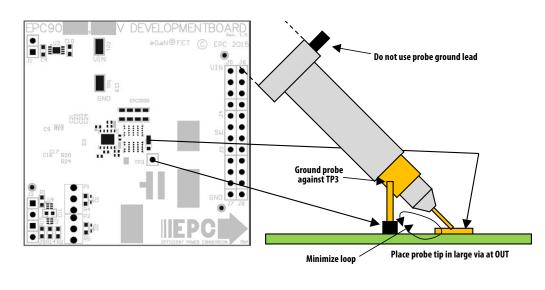


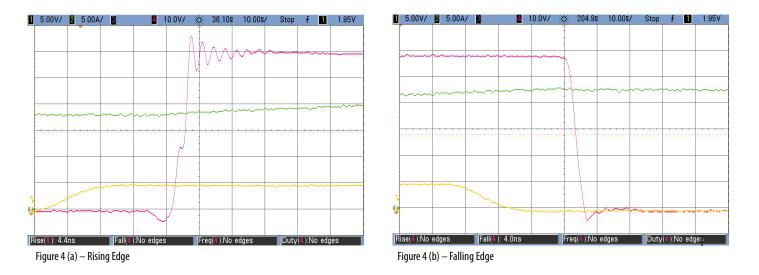
Figure 3: Proper Measurement of Switch Node – OUT

THERMAL CONSIDERATIONS

The EPC9060/61 development boards showcase the EPC2030/31 eGaN FETs. Although the electrical performance surpasses that for traditional Silicon devices, their relatively smaller size does magnify the thermal management requirements. These development boards are intended for bench evaluation with low ambient temperature and convection cooling. The addition of heat-sinking and forced air cooling

can significantly increase the current rating of these devices, but care must be taken to not exceed the absolute maximum die temperature of 150°C.

NOTE. The EPC9060/61 development boards do not have any current or thermal protection on board.



Typical Waveforms for V_{IN} = 60 V to 5V/20 A (300 kHz) Buck converter CH1: (V_{PWM}) Input logic signal – CH2: (I_{OUT}) Output inductor current – CH4: (V_{OUT}) Switch node voltage

Table 2 : Bill of Material

ltem	Qty	Reference	Part Description	Manufacturer	Part Number
1	3	C4, C10, C11	Capacitor, 1 μF, 10%, 25 V, X5R	Murata	GRM188R61E105KA12D
2	2	C16, C17	Capacitor, 100 pF, 5%, 50 V, NP0	Kemet	C0402C101K5GACTU
3	1	С9	Capacitor, 0.1 µF, 10%, 25 V, X5R	TDK	C1005X5R1E104K
4	1	C19	Capacitor, 1 μF, 10%, 25 V, X5R		C1005X5R1E105K
5	4	C21, C22, C23, C24	Capacitor, - see Table 3		See Table 3
6	2	D1, D2	Schottky Diode, 30 V	Diodes Inc.	SDM03U40-7
7	3	J1, J2, J9	Connector	FCI	68001-236HLF
8	1	J3, J4, J5, J6, J7, J8	Connector	FCI	68602-224HLF
9	2	Q1, Q2	eGaN [®] FET - see Table 3		See Table 3
10	1	R1	Resistor, 10.0 k, 5%, 1/10 W	Panasonic	ERJ-3GEY0R00V
11	2	R2, R15	Resistor, 0 Ω, 1/8 W	Stackpole	RMCF0603ZT0R00
12	1	R4	Resistor, 47 Ω, 1%, 1/10 W	Stackpole	RMFC0603FT47R0
13	1	R5	Resistor, 75 Ω, 1%, 1.10 W	Stackpole	RMCF0603FT75R0
14	4	R19, R20, R23, R24	Resistor, 0 Ω, 1/16 W	Stackpole	RMCF0402ZT0R00
15	2	TP1, TP2	Test Point	Keystone Elect	5015
16	1	TP3	Connector	1/40th of Tyco	4-103185-0
17	1	U1	I.C., Logic	Fairchild	NC7SZ00L6X
18	1	U2	I.C., Gate Driver	National	LM5113
19	1	U3	I.C., Regulator	Microchip	MCP1703T-5002E/MC
20	1	U4	I.C., Logic	Fairchild	NC7SZ08L6X
21	0	R14	Optional Resistor		
22	0	D3	Optional Diode		
23	0	P1, P2	Optional Potentiometer		

Table 3 : Variable BOM Components

Board Number	ltem	Qty	Reference	Part Description	Manufacturer	Part Number
FRCOOGO	5	4	C21, C22, C23, C24	Capacitor, 4.7 μ F, 50 V ±10%, X5R	TDK	C2012X5R1H475K125AB
EPC9060	9	2	Q1, Q2	eGaN® FET	EPC	EPC2030
	5	4	C21, C22, C23, C24	Capacitor, 1 μF, 100 V ±10%, X7S	TDK	CGA4J3X7S2A105K125AE
EPC9061	9	2	Q1, Q2	eGaN® FET	EPC	EPC2031

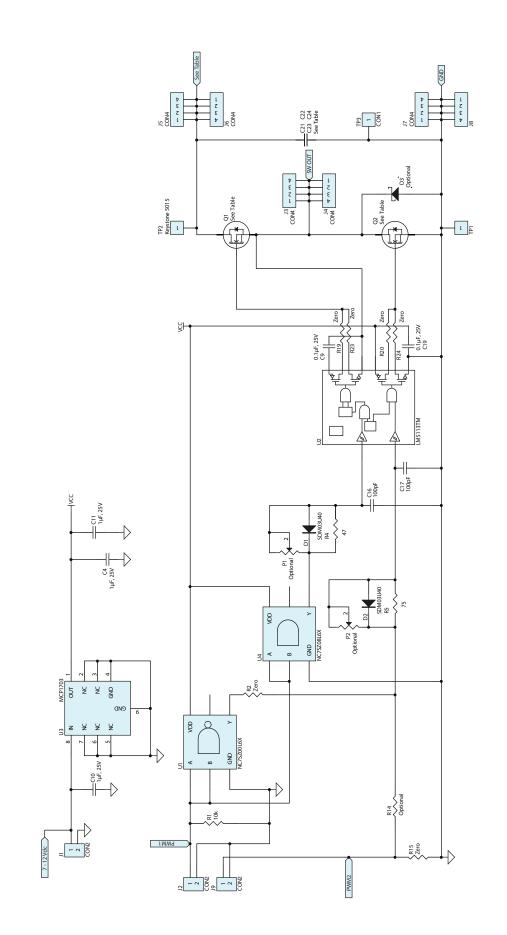


Figure 5: Development Board Schematic

For More Information:

Please contact info@epc-co.com or your local sales representative

Visit our website: www.epc-co.com

Sign-up to receive EPC updates at bit.ly/EPCupdates or text "EPC" to 22828



DIDE-Key

EPC Products are distributed through Digi-Key. **www.digikey.com**

Demonstration Board Notification

The EPC9060/61 board is intended for product evaluation purposes only. It is not intended for commercial use nor is it FCC approved for resale. Replace components on the Evaluation Board only with those parts shown on the parts list (or Bill of Materials) in the Quick Start Guide. Contact an authorized EPC representative with any questions. This board is intended to be used by certified professionals, in a lab environment, following proper safety procedures. Use at your own risk.

As an evaluation tool, this board is not designed for compliance with the European Union directive on electromagnetic compatibility or any other such directives or regulations. As board builds are at times subject to product availability, it is possible that boards may contain components or assembly materials that are not RoHS compliant. Efficient Power Conversion Corporation (EPC) makes no guarantee that the purchased board is 100% RoHS compliant.

The Evaluation board (or kit) is for demonstration purposes only and neither the Board nor this Quick Start Guide constitute a sales contract or create any kind of warranty, whether express or implied, as to the applications or products involved.

Disclaimer: EPC reserves the right at any time, without notice, to make changes to any products described herein to improve reliability, function, or design. EPC does not assume any liability arising out of the application or use of any product or circuit described herein; neither does it convey any license under its patent rights, or other intellectual property whatsoever, nor the rights of others.